



# VEC2408 — N-Channel Silicon MOSFET

## General-Purpose Switching Device Applications

### Features

- The best suited for load switching applications.
- Low ON-resistance.
- Composite type facilitating high-density mounting.
- 1.8V drive.
- Mounting high 0.75mm.

### Specifications

#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		20	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±12	V
Drain Current (DC)	I <sub>D</sub>		3.5	A
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	14	A
Allowable Power Dissipation	P <sub>D</sub>	Mounted on a ceramic board (900mm <sup>2</sup> ×0.8mm)1unit	0.9	W
Total Dissipation	P <sub>T</sub>	Mounted on a ceramic board (900mm <sup>2</sup> ×0.8mm)	1.0	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

#### Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> =1mA, V <sub>GS</sub> =0V	20			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V			1	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	0.4		1.3	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =1.5A	2.4	4		S
Static Drain-to-Source On-State Resistance	R <sub>DS(on)1</sub>	I <sub>D</sub> =2A, V <sub>GS</sub> =4V	37	47	60	mΩ
	R <sub>DS(on)2</sub>	I <sub>D</sub> =1A, V <sub>GS</sub> =2.5V	42	61	85	mΩ
	R <sub>DS(on)3</sub>	I <sub>D</sub> =0.5A, V <sub>GS</sub> =1.8V	47	79	118	mΩ
	R <sub>DS(on)4</sub>	I <sub>D</sub> =0.1A, V <sub>GS</sub> =1.4V	72	167	540	mΩ
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =10V, f=1MHz		400		pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =10V, f=1MHz		92		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	V <sub>DS</sub> =10V, f=1MHz		85		pF

Marking : CK

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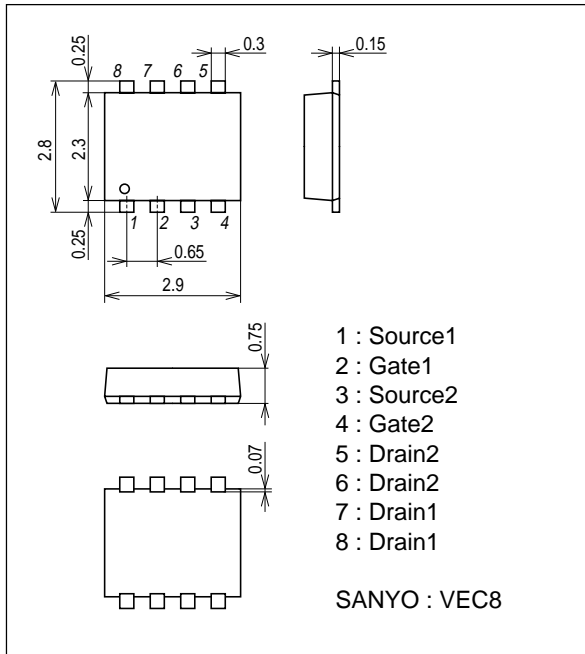
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		11		ns
Rise Time	$t_r$	See specified Test Circuit.		58		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit.		58		ns
Fall Time	$t_f$	See specified Test Circuit.		58		ns
Total Gate Charge	$Q_g$	$V_{DS}=10V, V_{GS}=4V, I_D=3.5A$		6		nC
Gate-to-Source Charge	$Q_{gs}$	$V_{DS}=10V, V_{GS}=4V, I_D=3.5A$		0.8		nC
Gate-to-Drain "Miller" Charge	$Q_{gd}$	$V_{DS}=10V, V_{GS}=4V, I_D=3.5A$		2.2		nC
Diode Forward Voltage	$V_{SD}$	$I_S=3.5A, V_{GS}=0V$		0.85	1.2	V

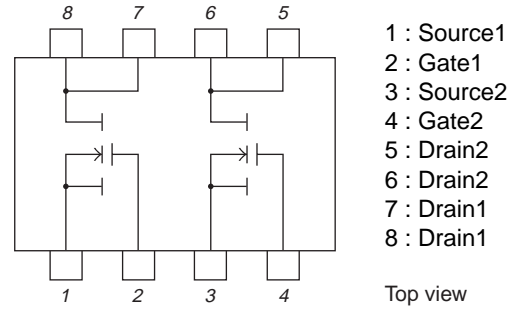
## Package Dimensions

unit : mm (typ)

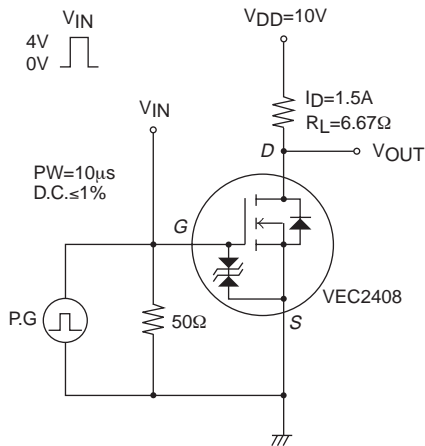
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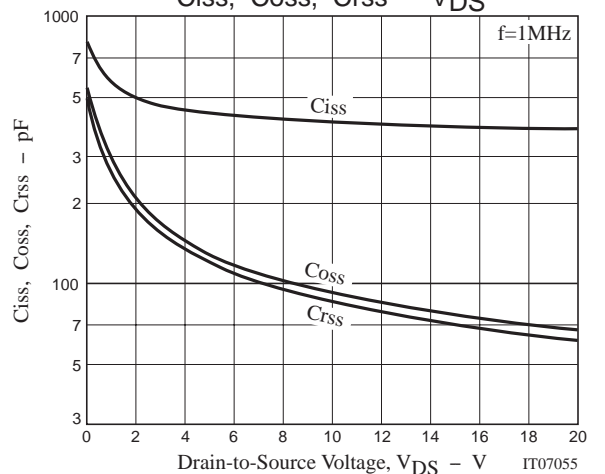
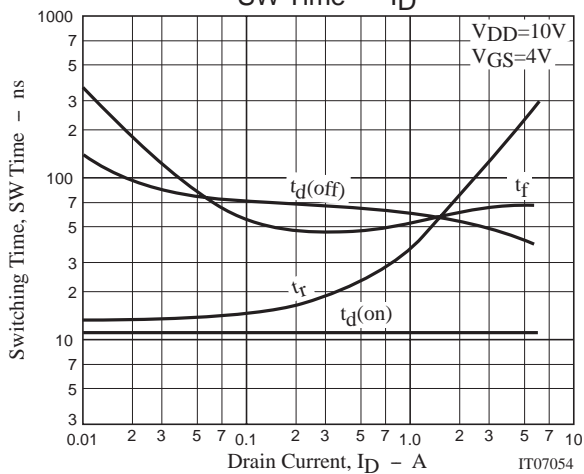
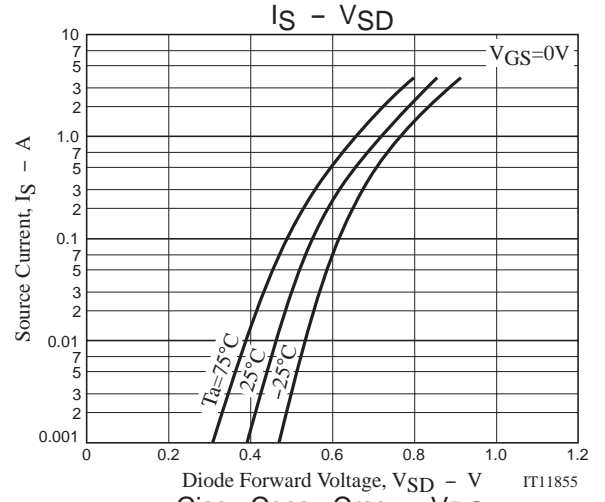
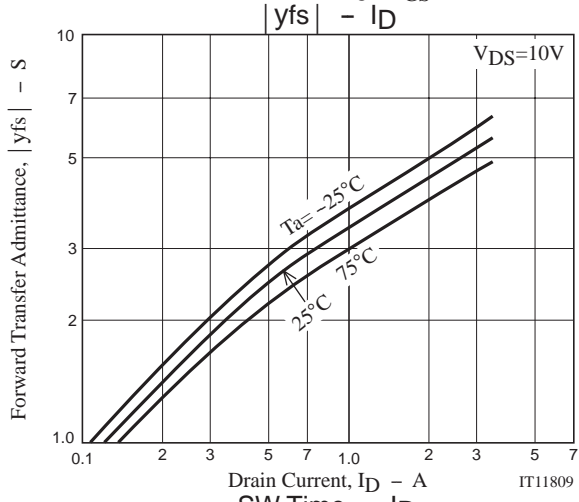
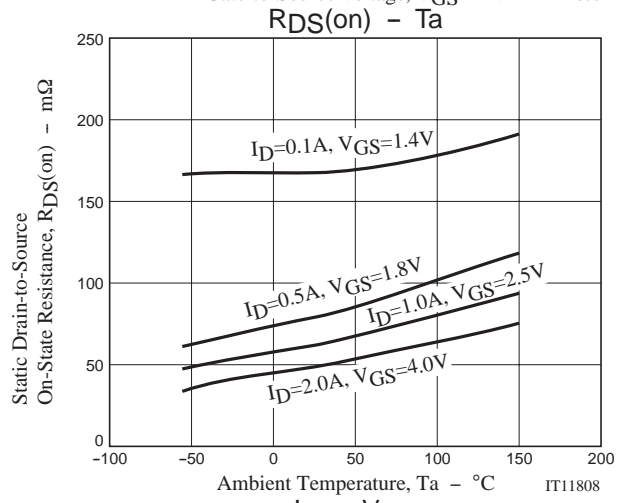
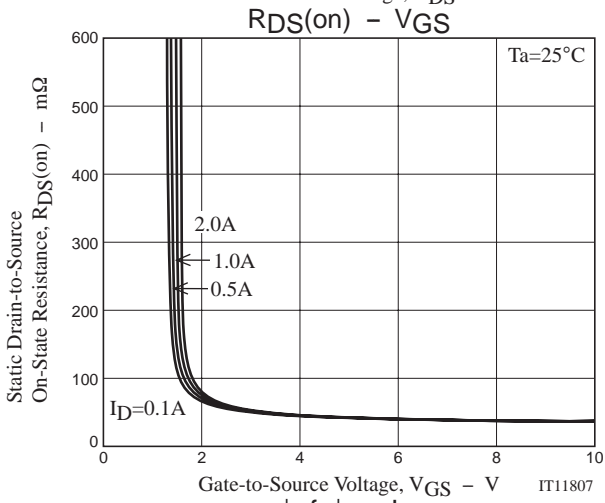
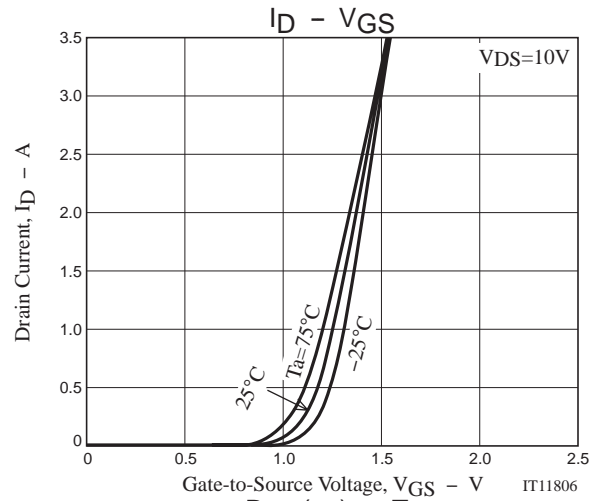
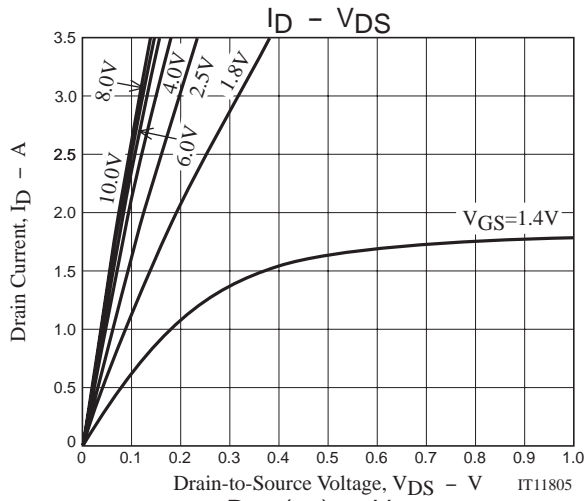
## Electrical Connection

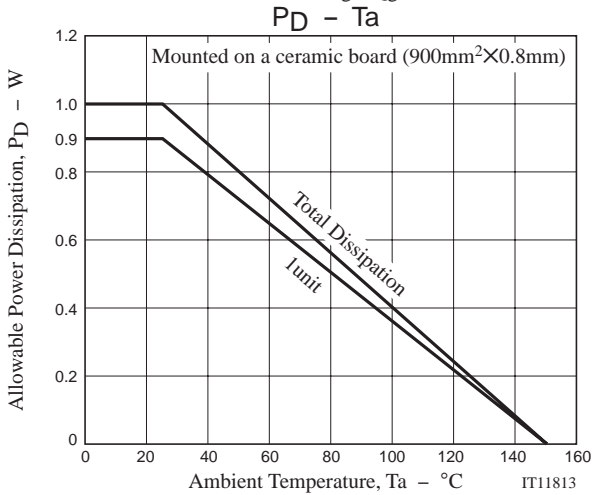
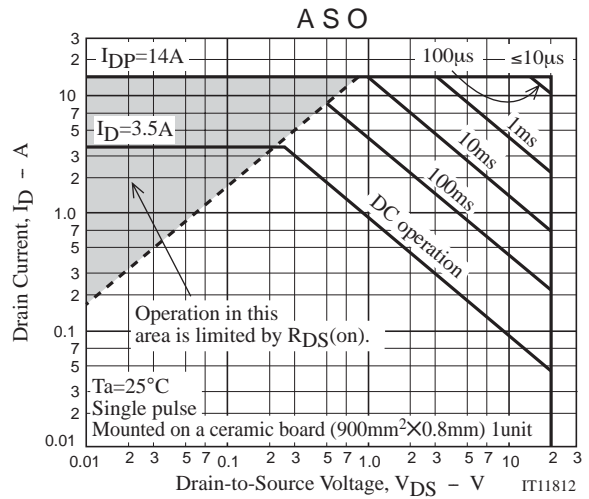
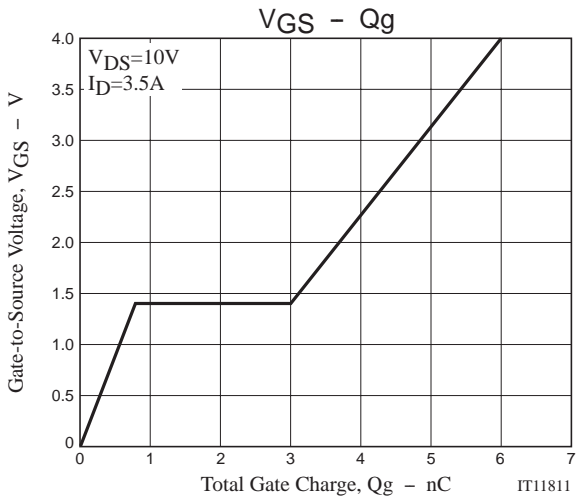


## Switching Time Test Circuit



# VEC2408





Note on usage : Since the VEC2408 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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